

FIG. 2
Related Art

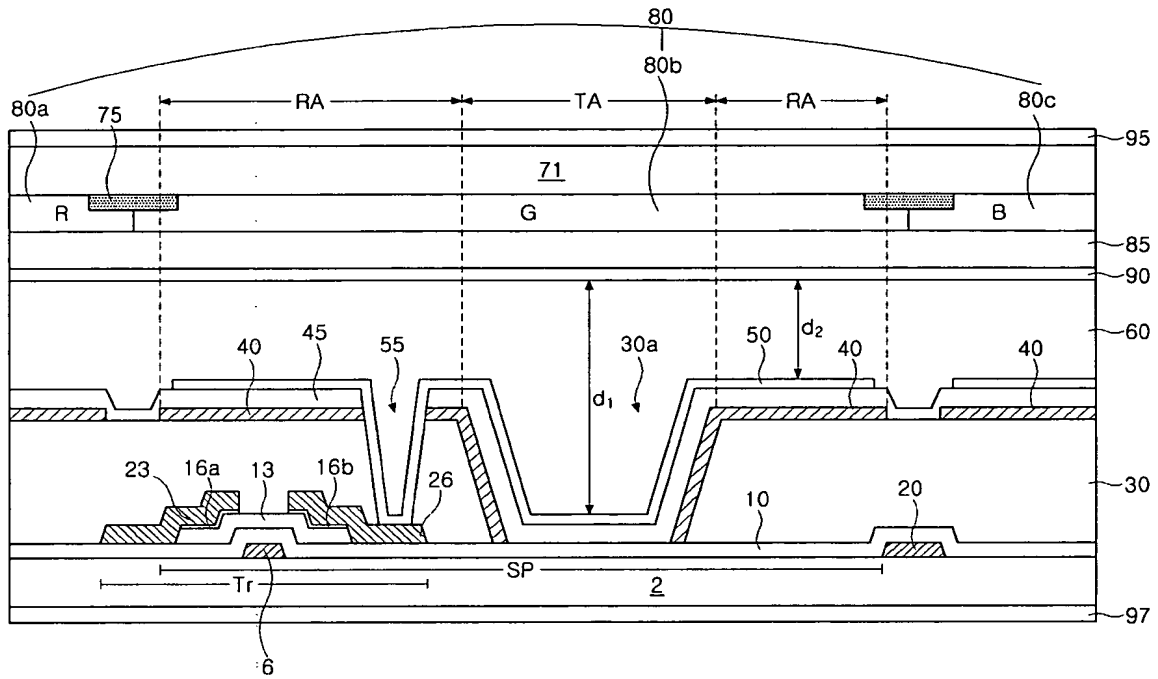


FIG. 3
Related Art

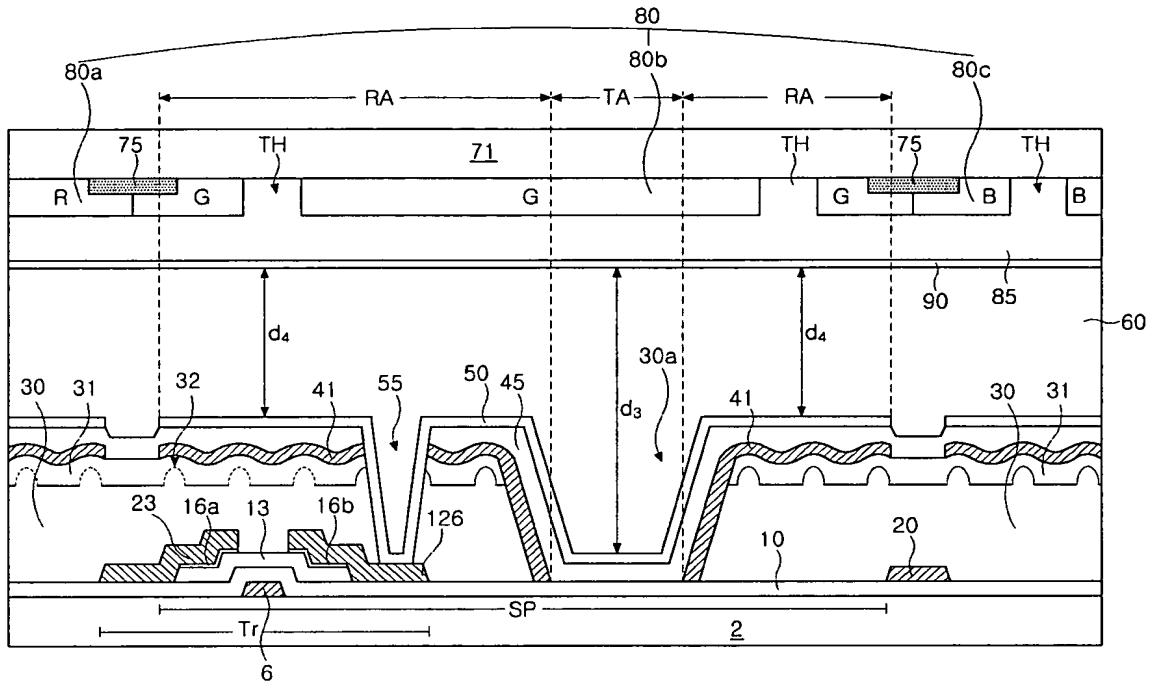
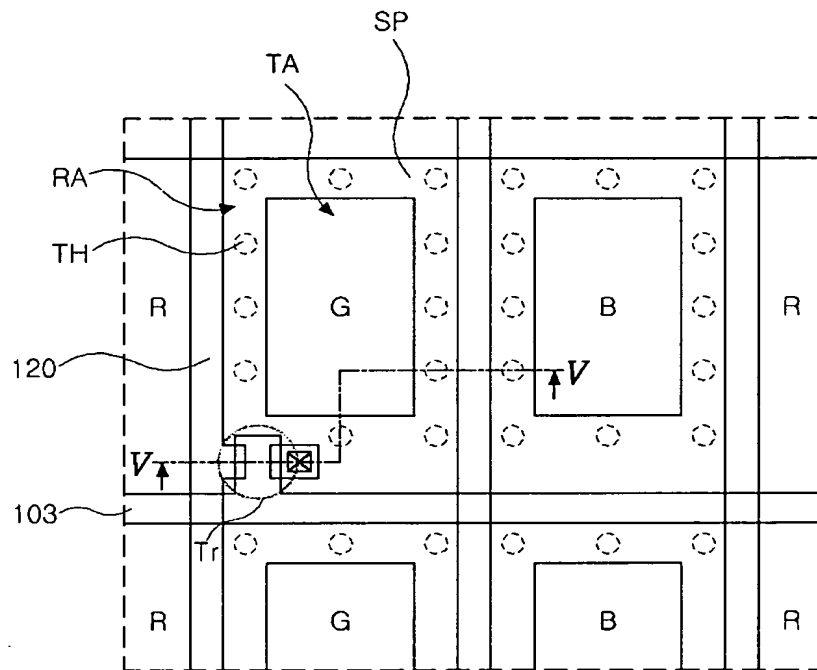


FIG. 4



[illegible]

FIG. 7A

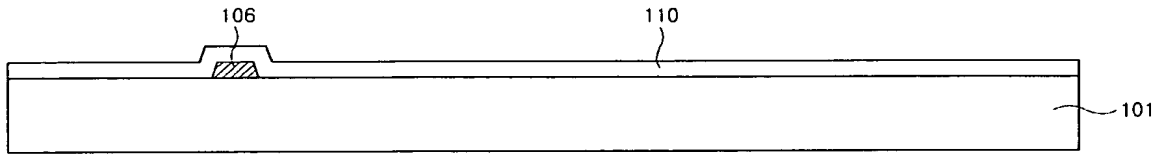


FIG. 7B

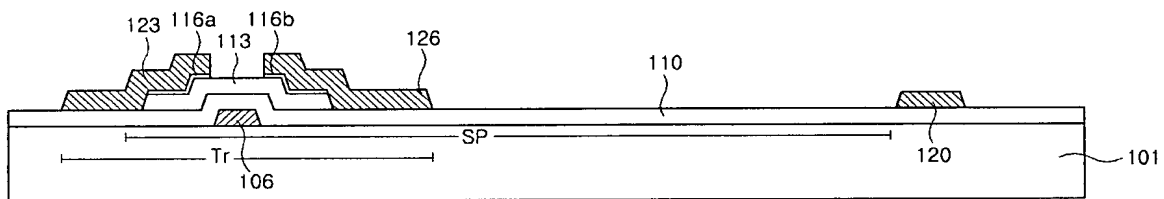


FIG. 7C

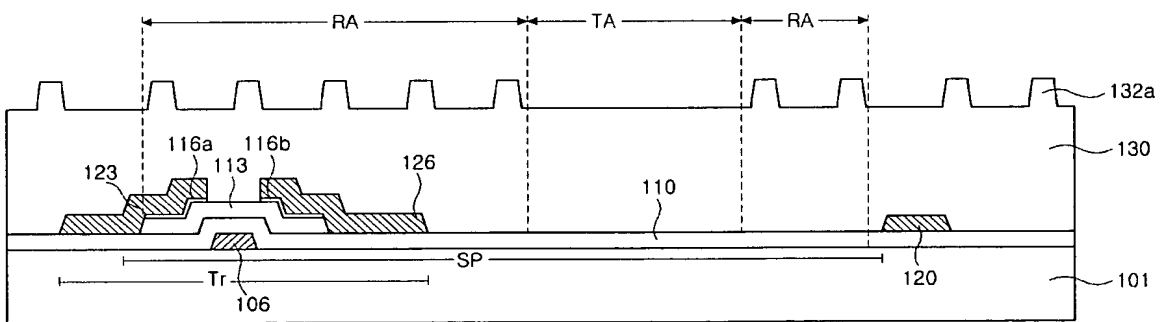


FIG. 7D

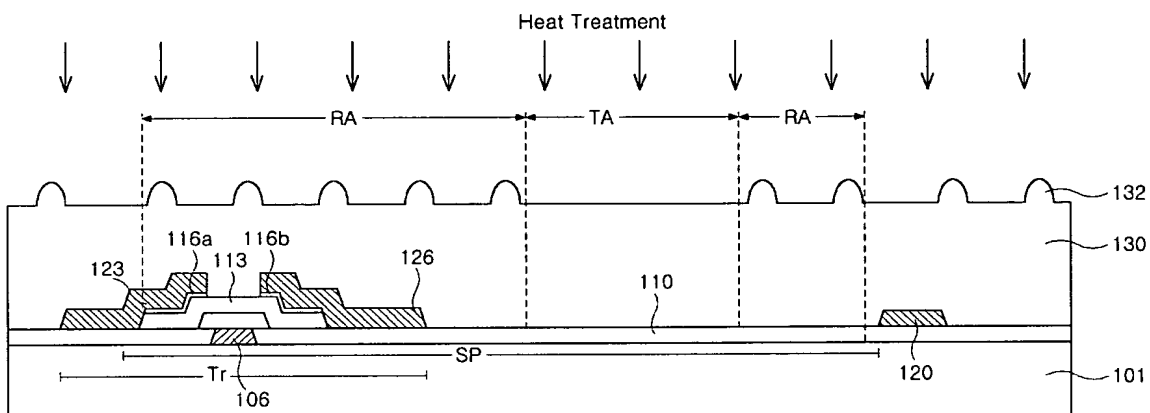


FIG. 7E

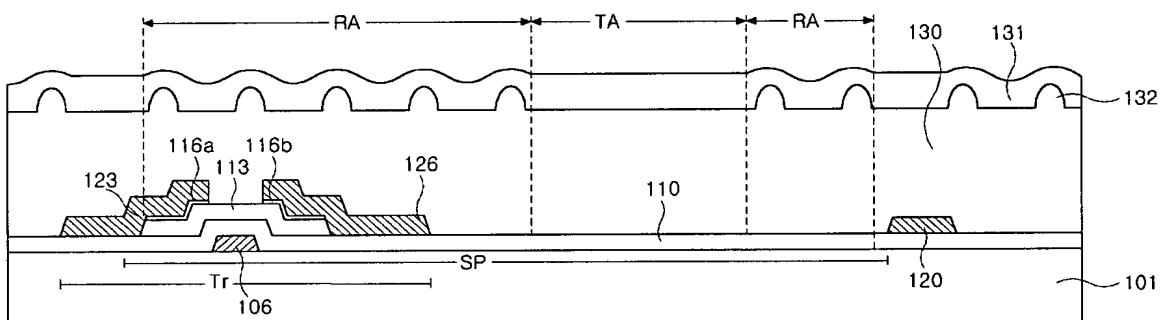


FIG. 7F

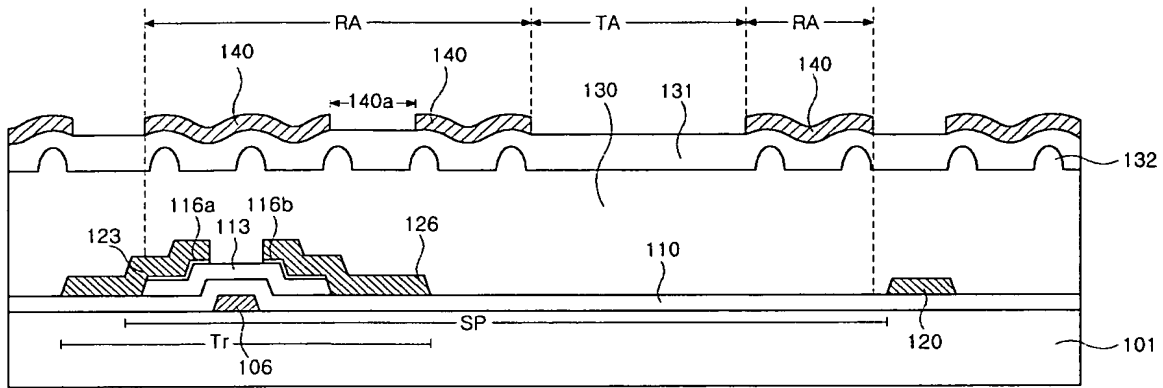
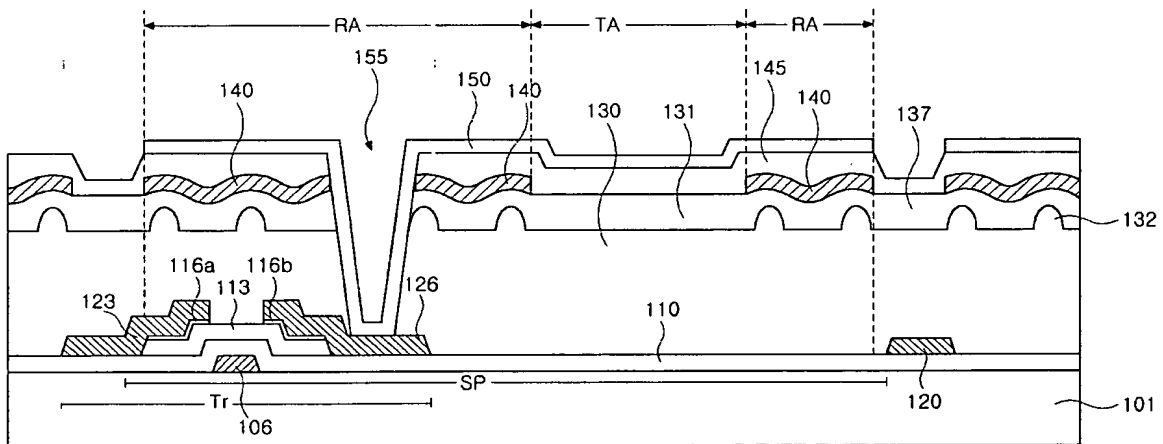


FIG. 7G



dry etching

RA TA RA

233

230

223 216a 216b 213 226

210

201

220

Tr SP

206

FIG. 8C

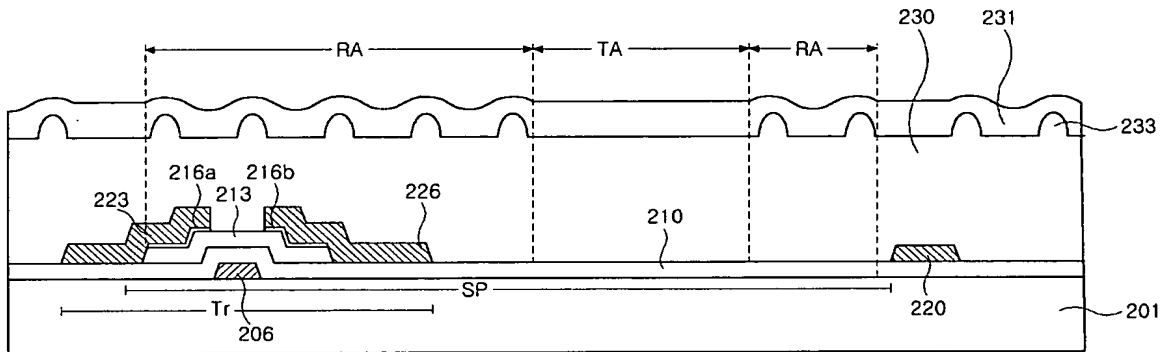
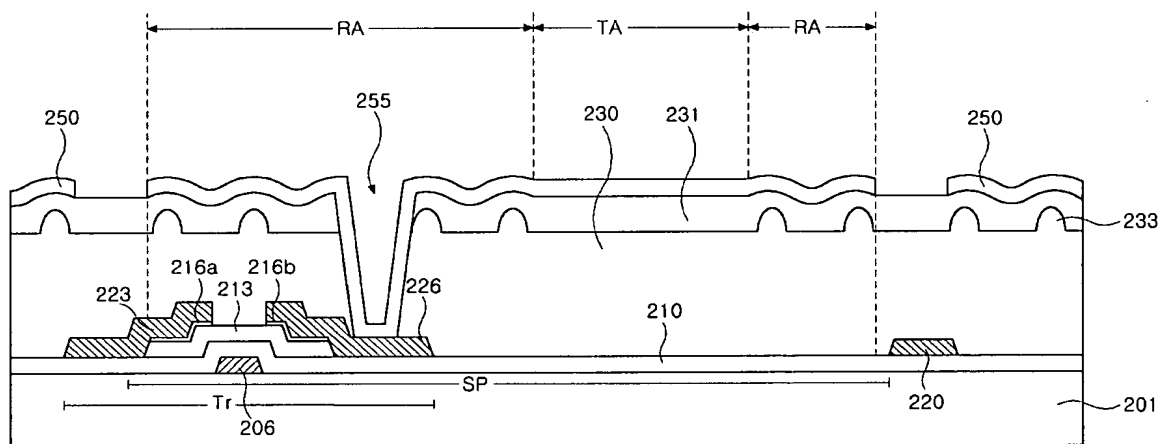


FIG. 8D



This diagram shows a plan view of the semiconductor device. It features a rectangular substrate labeled 171. On the top edge of the substrate, there are two rectangular regions labeled 175, which are filled with a stippled pattern. A horizontal line with arrows at both ends, labeled SP, spans the distance between the two regions 175.

Figure 1 is a plan view of a color filter 170. The color filter 170 includes a series of subpixels 180a, 180b, and 180c. Each subpixel 180a, 180b, and 180c contains a color layer (R, G, or B) and a transparent conductive layer (TH). The subpixels 180a, 180b, and 180c are separated by a spacer (SP) and a common electrode (175).

[illegible]